

Serial No. 09/493,819

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Docket No. T36-119817M/KOH

D1
C.M.D. emitting layer, such that, said first In composition ratio, X, at said second interface becomes substantially equal to a second In composition ratio, Y, of said light-emitting layer.

3. (Three Times Amended) A group III nitride compound semiconductor device of a successively laminated structure, comprising:

a substrate;

a buffer layer formed directly on said substrate and having a buffer layer lattice constant;

an intervening layer formed directly on said buffer layer, said intervening layer comprising $\text{Al}_a\text{Ga}_b\text{In}_{1-a-b}\text{N}$, where $0 < a < 1$, $0 < b < 1$, and $a + b < 1$; and

D2 a light-emitting layer formed directly on said intervening layer, said light-emitting layer comprising $\text{In}_Y\text{Ga}_{1-Y}\text{N}$, where $0 < Y < 1$, and having a second layer lattice constant,

wherein composition ratios of at least Al and In of said intervening layer change from a first interface with said buffer layer to a second interface with said light-emitting layer, such that, a first lattice constant of said intervening layer at said first interface changes to a second lattice constant that is substantially equal to a lattice constant of said light-emitting layer.

5. (Amended) A group III nitride compound semiconductor device according to claim 3, wherein said composition ratios of at least Al and In of said intervening layer change continuously or intermittently in a direction toward said light-emitting layer from said first interface with said buffer layer, so that, a band gap at said second interface of said intervening layer is wider than a band gap of said light-emitting layer.

D3 6. (Twice Amended) A group III nitride compound semiconductor device according to claim 3, wherein said composition ratio of at least Al of said intervening layer is changed continuously or intermittently in the direction toward said light-emitting layer from said first interface with said buffer layer, so that, a band gap at said second interface of said intervening layer is wider than a band gap of said second layer.